

1986 GaAs REL WORKSHOP PROGRAM, October 27, 1986, GRENELEFE, FLORIDA

DRIFT AND UNPREDICTABILITY IN THE D.C. AND MICROWAVE CHARACTERISTICS OF GaAs MESFETS DUE TO SURFACE STATES, P. H. Ladbroke and S. R. Blight, GEC Research Ltd. Hirst Research Centre, United Kingdom

SUPPRESSION OF DEEP LEVEL TRAPPING RELATED EFFECTS IN GaAs MESFETS USING A BURIED CHANNEL STRUCTURE, L. Forbes and P. Canfield, Oregon State University

METHODS TO SCREEN GaAs MESFETS WITH RF GAIN DRIFT PROBLEM, Guo-Gang Zhou, Tai Gwo, Harry Fujim.oto, Deon Glajchen, and Kris Jones, Gould, Microwave Product Division

PARAMETRIC DRIFT MECHANISMS IN GOLD METALLIZED MESFETS, S. Zaki and R. Ellsworth, Avantek

HIGH TEMPERATURE RELIABILITY OF GaAs BIPOLAR DEVICES, D. L. Plumton, L.T. Tran, H. T. Yuan, and J. Central Research Laboratories, Texas Instruments

RELIABILITY AND ELECTROMIGRATION PHENOMENA OF HIGH POWER MESFETS, K. K. Yu, S. K. Wang, and W. E. Klatskin, Hughes Aircraft Company, Torrance Research Center

GaAs INTEGRATED CIRCUIT RELIABILITY STUDIES AT FORD MICROELECTRONICS, Thomas E. Paquette, C. S. BhaBker, J. Cyr, and R. Rosenberry, Ford Microelectronics

ELECROSTATIC DISCHARGE (ESD) THRESHOLDS FOR GaAs FETS, W.T. Anderson, Naval Research Laboratory and E. W. Chase, Bell Communications Research

MANUFACTURING TECHNOLOGY FOR SOLID-STATE MICROWAVE SYSTEMS (GaAs MT) - RELIABILITY ISSUES, Lawrence R. Whicker, J. Zingaro, and S. H. Lee, Westinghouse ATD, Baltimore

ACCELERATED RF LIFE TESTING OF A C-BAND POWER AMPLIFIER MMIC, R. J. Finke and D. J. LaCombe, General Electric Company, Syracuse

RELIABILITY INVESTIGATION OF GaAs PRESCALER IC, M. Katsumata, N. Tanino, K. Maemura, Y. Nakajima, Y. Mitsui, O. Ishihara, and Y. Onodera, LSI Research & Development Lab, Kitaitami Works, Mitsubishi Electric Corp.

IMPROVEMENT OF ALPHA-PARTICLE-INDUCED SOFT-ERROR IMMUNITY IN GaAs SRAM BY A BURIED P-LAYER, Y. Umemoto, N. Masuda, J. Shigets, N. Hashimoto, and K. Mitsusada, Central Research Laboratory, Hitachi

EFFECTS OF NEUTRON RADIATION ON GaAs HETEROJUNCTION BIPOLAR TRANSISTORS, L. T. Tran, H. T. Yuan, J. F. Salzman, Central Research Laboratories, Texas Instruments and W. T. Anderson, Naval Research Laboratory

A UNIFIED MODEL OF SUBSURFACE BURNOUT IN GaAs MESFET AND MODFET STRUCTURES, F. A. Buot, W. T. Anderson, A. Christou, and K. J. Sleger, Naval Research Laboratory

STRUCTURE OF OHMIC CONTACTS AT AlGaAs/GaAs MODFET CHANNEL INTERFACE, A. Ezis and A. K. Rai, Universal Energy Systems, and D. W. Langer, AFWAL/AADL, Wright-Patterson AFB

RELIABILITY CONSTRAINTS OF HIGH ELECTRON MOBILITY TRANSISTORS, A. Christou and F. A. Buot, Naval Research Laboratory

RELIABILITY EVALUATION OF V-BAND HENT DEVICES, R. J. Finke and D. J. LaCombe, General Electric, Syracuse

RELIABILITY CHARACTERIZATION OF 7.5 GHz GaAs POWER MESFETS, W. A. Koziarz and E. A. Doyle Jr., RADC, Griffiss AFB, NY

A RADIATION-HARDENED GaAs TECHNOLOGY PROGRAM FOR SPACE SYSTEM APPLICATIONS, H. Hwang and I. Kohlberg, General Electric, Philadelphia

TOTAL DOSE and NEUTRON RADIATION HARDNESS of HARRIS GaAs DEVICES, R. Gokhale, W. O'Mara and Van N. Vonno, Harris Corp., Melbourne, FL.